

etching at least said insulating layer thereby forming a surface with a first semiconductor area separated from a second semiconductor area by an unbroken insulating area;

doping the surface, such that said surface includes a first doped semiconductor area in the first semiconductor area electrically isolated from a second doped semiconductor area in the second semiconductor area by the unbroken insulator area;

etching a trough in the surface of the first semiconductor area; and

forming a slot in the trough, the slot extending through the semiconductor die.

Another version of the amended claim, marked up to show all of the changes relative to the previous version of the claims, is filed herewith on pages separate from the amendment, in accordance with 37 CFR § 1.121(c)(1)(ii).

Please add new claims 36-40 as follows:

36. (NEW) The process of Claim 32 wherein the unbroken insulating area extends around the first doped semiconductor area.

37. (NEW) The process of Claim 32 wherein said forming, at a surface of a semiconductor die, at least an insulating layer comprises growing a gate oxide layer.

38. (NEW) The process of Claim 37 wherein said forming, at a surface of a semiconductor die, at least an insulating layer further comprises depositing a gate electrode layer.

39. (NEW) The process of Claim 38 further comprising depositing a tantalum cavitation layer.